

# MCT2M, MCT2EM, MCT210M, MCT271M Phototransistor Optocouplers

## Features

- UL recognized (File # E90700, Vol. 2)
- IEC60747-5-2 recognized (File # 102497)
  - Add option V (e.g., MCT2VM)

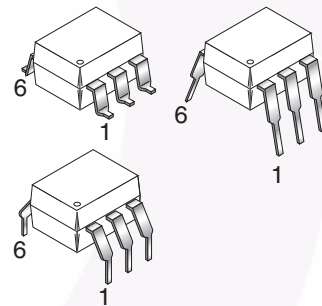
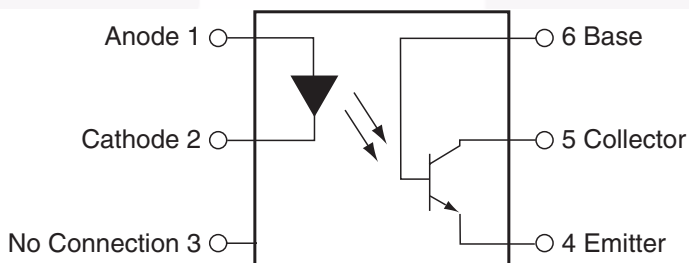
## Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

## Description

The MCT2XXM series optoisolators consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

## Schematic



## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
<b>TOTAL DEVICE</b>			
$T_{STG}$	Storage Temperature	-40 to +150	°C
$T_{OPR}$	Operating Temperature	-40 to +100	°C
$T_{SOL}$	Lead Solder Temperature	260 for 10 sec	°C
$P_D$	Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$	250	mW
	Derate above $25^\circ\text{C}$	2.94	mW/°C
<b>EMITTER</b>			
$I_F$	DC/Average Forward Input Current	60	mA
$V_R$	Reverse Input Voltage	3	V
$I_F(pk)$	Forward Current – Peak (300 $\mu\text{s}$ , 2% Duty Cycle)	3	A
$P_D$	LED Power Dissipation @ $T_A = 25^\circ\text{C}$	120	mW
	Derate above $25^\circ\text{C}$	1.41	mW/°C
<b>DETECTOR</b>			
$I_C$	Collector Current	50	mA
$V_{CEO}$	Collector-Emitter Voltage	30	V
$P_D$	Detector Power Dissipation @ $T_A = 25^\circ\text{C}$	150	mW
	Derate above $25^\circ\text{C}$	1.76	mW/°C

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)**Individual Component Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Units
<b>EMITTER</b>							
$V_F$	Input Forward Voltage	$I_F = 20\text{mA}$	MCT2M MCT2EM MCT271M		1.25	1.50	V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$ , $I_F = 40\text{mA}$	MCT210M		1.33		
$I_R$	Reverse Leakage Current	$V_R = 3.0\text{V}$	MCT2M MCT2EM MCT271M		0.001	10	$\mu\text{A}$
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$ , $V_R = 6.0\text{V}$	MCT210M				
<b>DETECTOR</b>							
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0\text{mA}$ , $I_F = 0$	ALL	30	100		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M				
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}$ , $I_F = 0$	MCT2M MCT2EM MCT271M	70	120		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	30			
$BV_{ECO}$	Emitter-Collector Breakdown Voltage	$I_E = 100\mu\text{A}$ , $I_F = 0$	MCT2M MCT2EM MCT271M	7	10		V
		$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	6	10		
$I_{CEO}$	Collector-Emitter Dark Current	$V_{CE} = 10\text{V}$ , $I_F = 0$	ALL		1	50	nA
		$V_{CE} = 5\text{V}$ , $T_A = 0^\circ\text{C} - 70^\circ\text{C}$				30	$\mu\text{A}$
$I_{CBO}$	Collector-Base Dark Current	$V_{CB} = 10\text{V}$ , $I_F = 0$	ALL			20	nA
$C_{CE}$	Capacitance	$V_{CE} = 0\text{V}$ , $f = 1\text{MHz}$	ALL		8		pF

\*All typical  $T_A = 25^\circ\text{C}$ **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ*	Max	Units
$V_{ISO}$	Input-Output Isolation Voltage	$f = 60\text{Hz}$ , $t = 1 \text{ sec.}$	7500			Vac(pk)
$R_{ISO}$	Isolation Resistance	$V_{I-O} = 500 \text{ VDC}$	$10^{11}$			$\Omega$
$C_{ISO}$	Isolation Capacitance			0.2	2	pF

\*All typicals at  $T_A = 25^\circ\text{C}$

**Electrical Characteristics** (Continued) ( $T_A = 25^\circ\text{C}$  unless otherwise specified)**Transfer Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
<b>DC CHARACTERISTICS</b>							
CTR	Output Collector Current	$T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M	150			%
		$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	MCT2M MCT2EM	20			
			MCT271M	45		90	
			MCT210M	50			
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{mA}, I_F = 16\text{mA}$	MCT2M MCT2EM MCT271M			0.4	V
		$I_C = 16\text{mA}, I_F = 32\text{mA}, T_A = 0^\circ\text{C} - 70^\circ\text{C}$	MCT210M				
<b>AC CHARACTERISTICS</b>							
$t_{on}$	AC Characteristic Saturated Turn-on Time from 5V to 0.8V	$I_F = 15\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = \text{Open (Fig. 11)}$	MCT2M MCT2EM		1.1		$\mu\text{s}$
		$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = 100\text{k}\Omega \text{ (Fig. 11)}$	MCT2M MCT2EM		1.3		
$t_{off}$	Saturated Turn-off Time from SAT to 2.0 V	$I_F = 15\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = \text{Open (Fig. 11)}$	MCT2M MCT2EM		50		$\mu\text{s}$
		$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 2\text{k}\Omega, R_B = 100\text{k}\Omega \text{ (Fig. 11)}$	MCT2M MCT2EM		20		
$t_{on}$	Turn-on Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		$\mu\text{s}$
$t_{off}$	Turn-off Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		$\mu\text{s}$
$t_r$	Rise Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		2		$\mu\text{s}$
$t_f$	Fall Time	$I_F = 10\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$	MCT2M MCT2EM		1.5		$\mu\text{s}$
$t_{on}$	Saturated turn-on time	$I_F = 16\text{mA}, R_L = 1.9\text{k}\Omega, V_{CC} = 5\text{V (Fig. 11)}$	MCT271M		1.0		$\mu\text{s}$
$t_{off}$	Saturated turn-off time (Approximates a typical TTL interface)				48		$\mu\text{s}$
$t_{on}$	Saturated turn-on time	$I_F = 16\text{mA}, R_L = 4.7\text{k}\Omega, V_{CC} = 5\text{V (Fig. 20)}$	MCT271M		1.0		$\mu\text{s}$
$t_{off}$	Saturated turn-off time (Approximates a typical low power TTL interface)				98		$\mu\text{s}$
$t_r$	Saturated rise time	$I_F = 16\text{mA}, R_L = 560\Omega, V_{CC} = 5\text{V (Fig. 11, 12)}$	MCT210M		1.0		$\mu\text{s}$
$t_f$	Saturated fall time				11		$\mu\text{s}$
$T_{PD(HL)}$	Saturated propagation delay – HIGH to LOW	$I_F = 16\text{mA}, R_L = 2.7\text{k}\Omega \text{ (Fig. 11, 12)}$	MCT210M		1.0		$\mu\text{s}$
$T_{PD(LH)}$	Saturated propagation delay – LOW to HIGH				50		$\mu\text{s}$
$t_r$	Non-saturated rise time	$I_C = 2\text{mA}, V_{CC} = 5\text{V}, R_L = 100\Omega \text{ (Fig. 11)}$	MCT210M		2		$\mu\text{s}$
$t_f$	Non-saturated fall time				2		$\mu\text{s}$
$t_{on}$	Non-saturated turn-on time	$I_C = 2\text{mA}, V_{CC} = 5\text{V}, R_L = 100\Omega \text{ (Fig. 20)}$	MCT271M		2	7	$\mu\text{s}$
$t_{off}$	Non-saturated turn-off time				2	7	$\mu\text{s}$

\*All typicals at  $T_A = 25^\circ\text{C}$

## Typical Performance Curves

Fig. 1 LED Forward Voltage vs. Forward Current

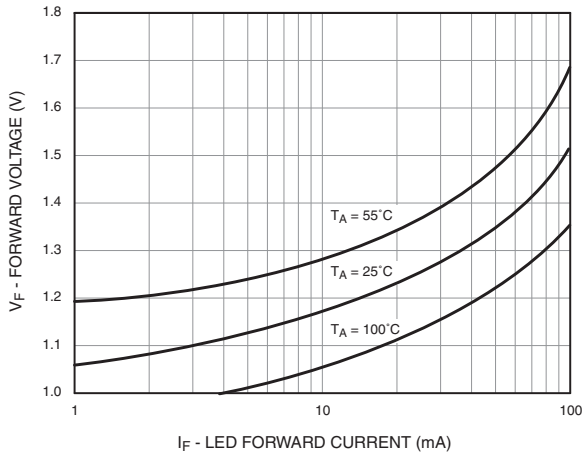


Fig. 2 Normalized CTR vs. Forward Current

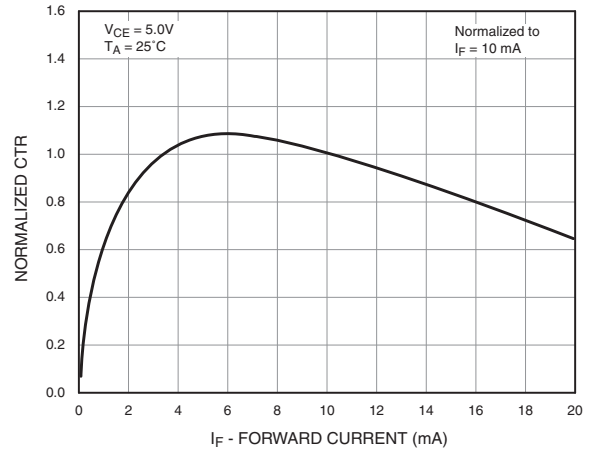


Fig. 3 Normalized CTR vs. Ambient Temperature

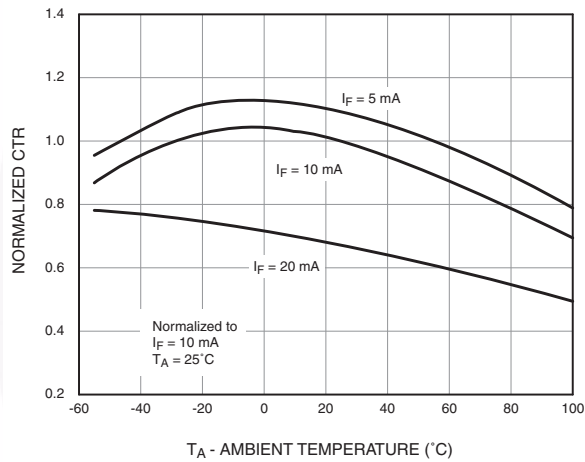


Fig. 4 CTR vs. RBE (Unsaturated)

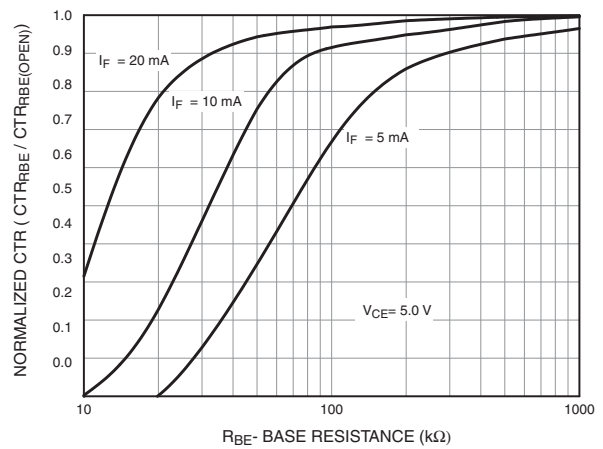


Fig. 5 CTR vs. RBE (Saturated)

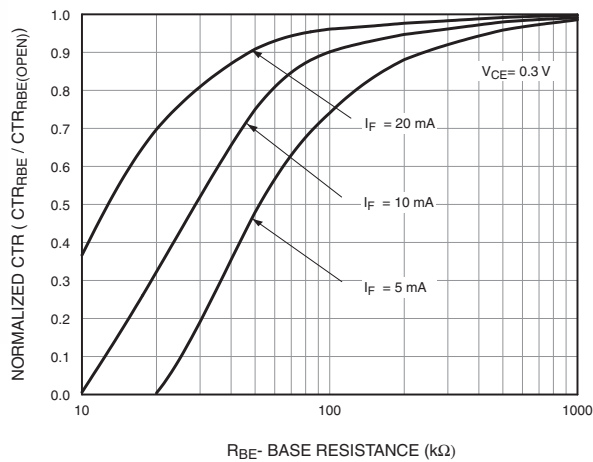
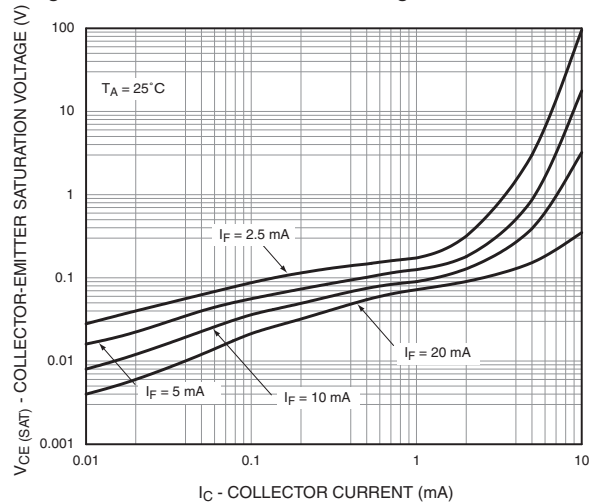


Fig. 6 Collector-Emitter Saturation Voltage vs Collector Current



Typical Performance Curves (Continued)

Fig. 7 Switching Speed vs. Load Resistor

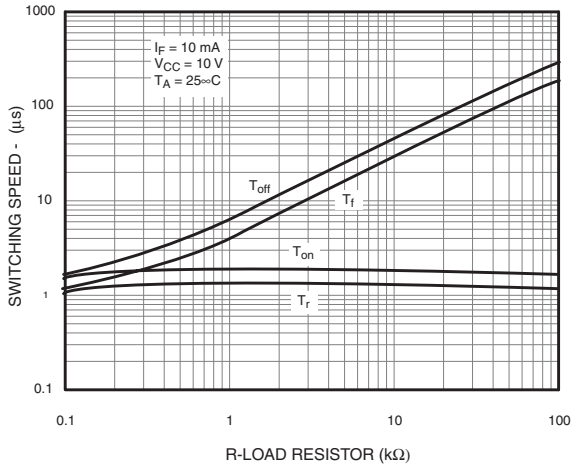


Fig. 8 Normalized  $t_{on}$  vs.  $R_{BE}$

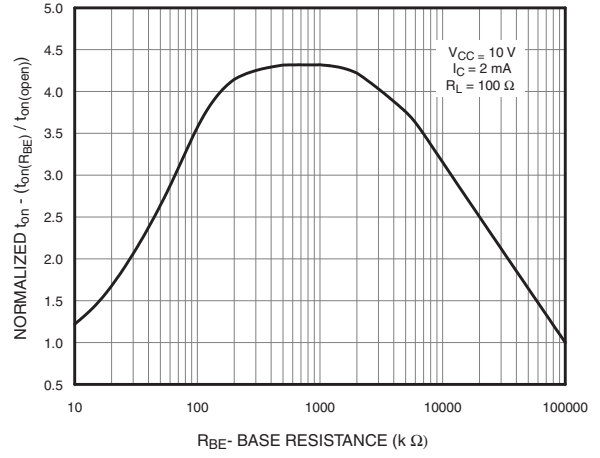


Fig. 9 Normalized  $t_{off}$  vs.  $R_{BE}$

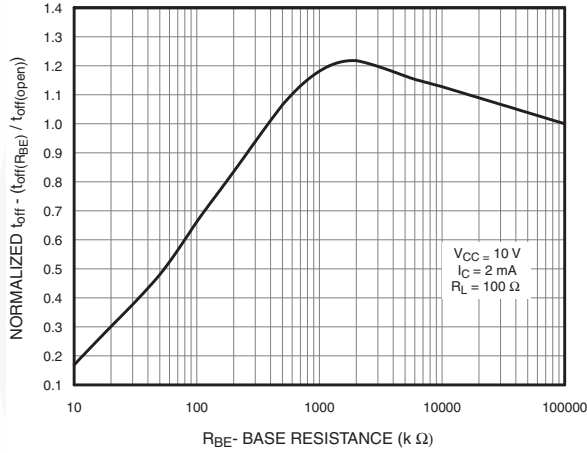
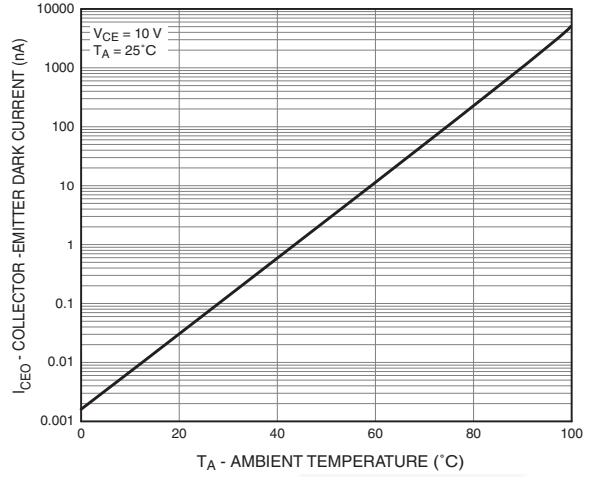


Fig. 10 Dark Current vs. Ambient Temperature



## Typical Electro-Optical Characteristics

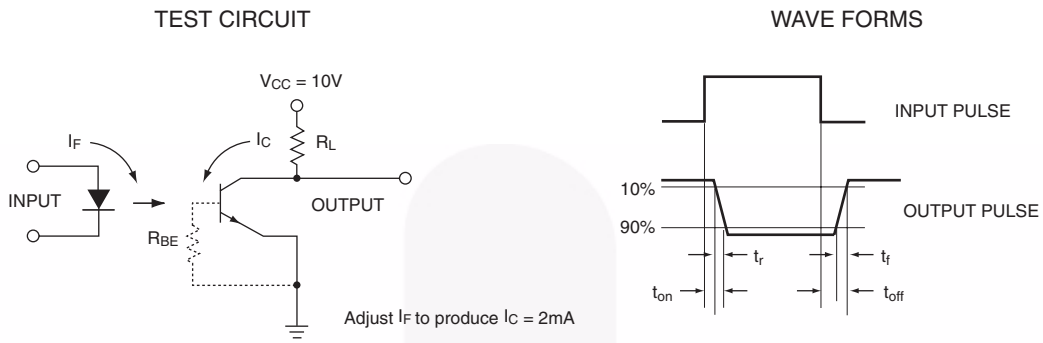


Figure 11. Switching Time Test Circuit and Waveforms

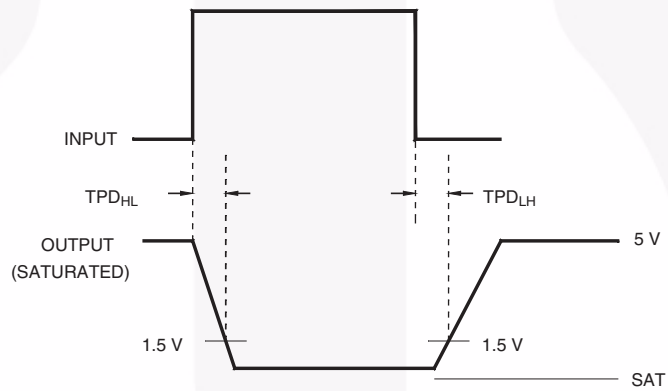
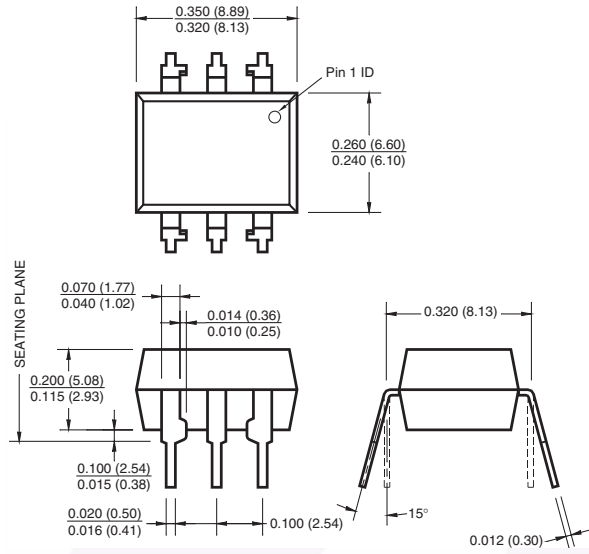


Figure 12. Switching Time Waveforms (MCT210M)

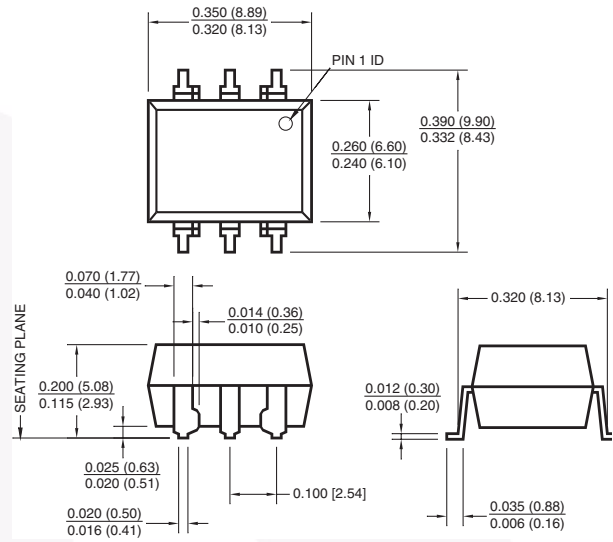


## Package Dimensions

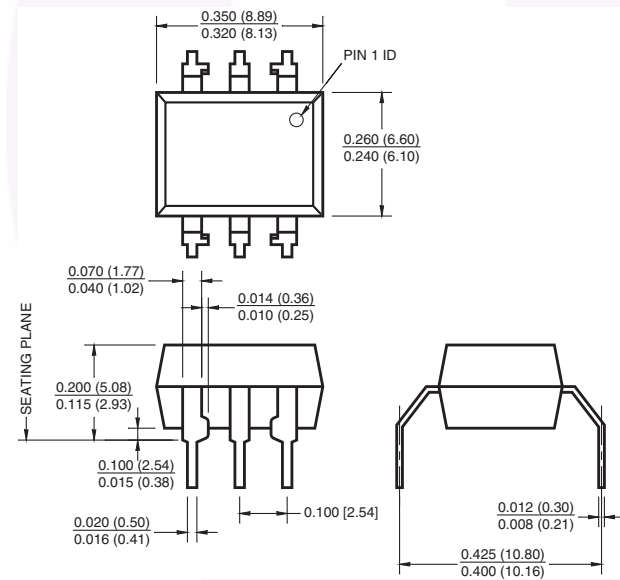
### Through Hole



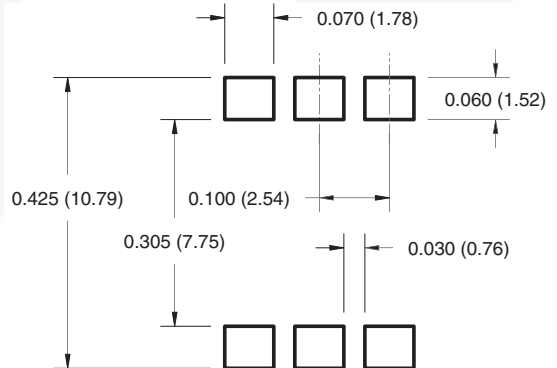
### Surface Mount



### 0.4" Lead Spacing



### Recommended Pad Layout for Surface Mount Leadform



### Note:

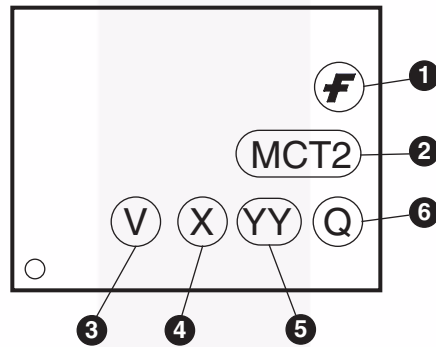
All dimensions are in inches (millimeters)



## Ordering Information

Option	Order Entry Identifier (Example)	Description
No suffix	MCT2M	Standard Through Hole Device (50 units per tube)
S	MCT2SM	Surface Mount Lead Bend
SR2	MCT2SR2M	Surface Mount; Tape and Reel (1,000 units per reel)
T	MCT2TM	0.4" Lead Spacing
V	MCT2VM	IEC60747-5-2
TV	MCT2TVM	IEC60747-5-2, 0.4" Lead Spacing
SV	MCT2SVM	IEC60747-5-2, Surface Mount
SR2V	MCT2SR2VM	IEC60747-5-2, Surface Mount, Tape and Reel (1,000 units per reel)

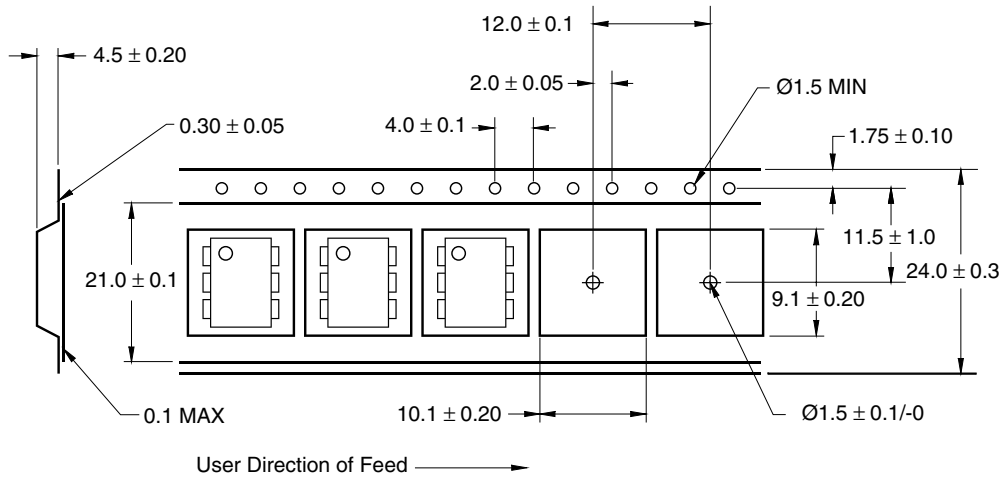
## Marking Information



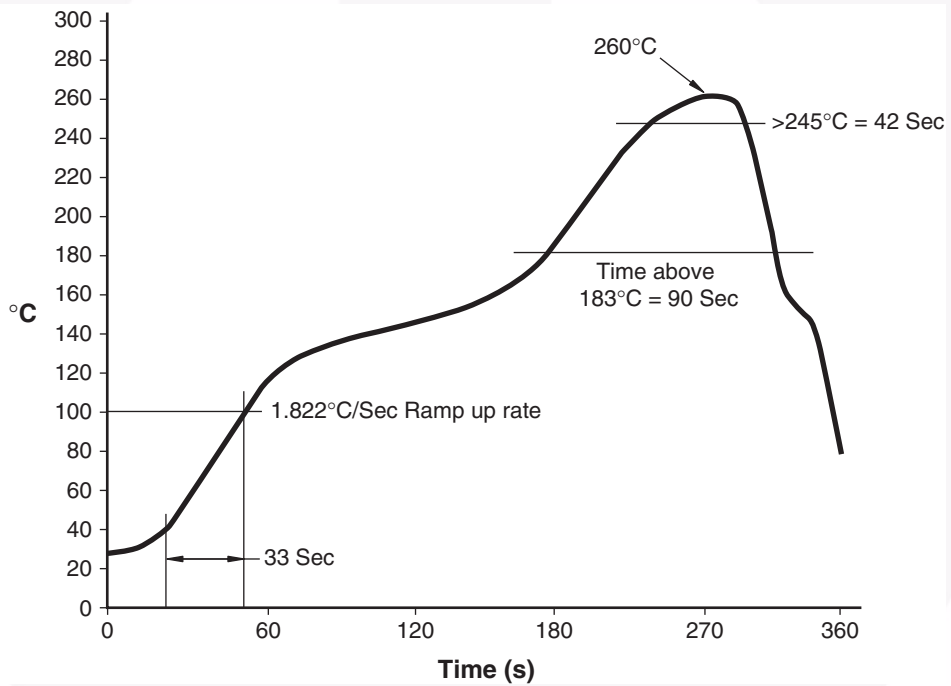
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

\*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

### Carrier Tape Specification




### Reflow Profile





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		SuperSOT™.8	

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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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